

Jan Muszalski

List of Publications by Year in descending order

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28
papers

319
citations

933264

10
h-index

839398

18
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29
all docs

29
docs citations

29
times ranked

334
citing authors

#	ARTICLE	IF	CITATIONS
1	Measurement of linewidth enhancement factor in self-assembled quantum dot semiconductor lasers emitting at 1310nm. Electronics Letters, 2004, 40, 428.	0.5	47
2	MBE growth of strain-compensated InGaAs/InAlAs/InP quantum cascade lasers. Journal of Crystal Growth, 2017, 466, 22-29.	0.7	37
3	The effect of pressure on the luminescence from GaAs/AlGaAs quantum wells. Semiconductor Science and Technology, 1994, 9, 2239-2246.	1.0	31
4	The influence of the growth rate and V/III ratio on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. Journal of Crystal Growth, 2009, 311, 4423-4432.	0.7	27
5	The influence of the growth temperature and interruption time on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. Journal of Crystal Growth, 2008, 310, 2785-2792.	0.7	24
6	Static phase diagrams of reconstructions for MBE-grown GaAs(001) and AlAs(001) surfaces. Thin Solid Films, 1995, 267, 54-57.	0.8	22
7	Molecular-beam epitaxy growth and characterization of mid-infrared quantum cascade laser structures. Microelectronics Journal, 2009, 40, 565-569.	1.1	22
8	Membrane external-cavity surface-emitting laser emitting at 1640nm. Optics Letters, 2020, 45, 539.	1.7	17
9	Highly efficient heat extraction by double diamond heat-spreaders applied to a vertical external cavity surface-emitting laser. Optical and Quantum Electronics, 2017, 49, 1.	1.5	16
10	Switchable double wavelength generating vertical external cavity surface-emitting laser. Optics Express, 2014, 22, 6447.	1.7	12
11	Photoluminescence mapping and angle-resolved photoluminescence of MBE-grown InGaAs/GaAs RC LED and VCSEL structures. Thin Solid Films, 2002, 412, 114-121.	0.8	10
12	A 95-nm-wide Tunable Two-Mode Vertical External Cavity Surface-Emitting Laser. IEEE Photonics Technology Letters, 2017, 29, 2215-2218.	1.3	9
13	High-Power 1770 nm Emission of a Membrane External-Cavity Surface-Emitting Laser. IEEE Journal of Quantum Electronics, 2021, 57, 1-6.	1.0	9
14	Pyrometric interferometry during MBE growth of laser heterostructures. Thin Solid Films, 2000, 367, 299-301.	0.8	8
15	The effect of the MBE growth rate on the surface phase diagram for GaAs (001). Thin Solid Films, 1995, 267, 51-53.	0.8	5
16	Dual-wavelength vertical external-cavity surface-emitting laser: strict growth control and scalable design. Applied Physics B: Lasers and Optics, 2016, 122, 1.	1.1	5
17	Nanoindentation of GaAs/AlAs distributed bragg reflector grown on GaAs substrate. Materials Science in Semiconductor Processing, 2020, 109, 104912.	1.9	5
18	Impact of strain on periodic gain structures in vertical external cavity surface-emitting lasers. Applied Physics B: Lasers and Optics, 2016, 122, 1.	1.1	4

#	ARTICLE	IF	CITATIONS
19	<title>GRIN SCH SQW AlGaAs/GaAs lasers grown by molecular beam epitaxy: modeling and operating characteristics</title>. , 1997, , .		2
20	Improvement of quantum efficiency of MBE grown AlGaAs/InGaAs/GaAs edge emitting lasers by optimisation of construction and technology. Vacuum, 2007, 82, 383-388.	1.6	2
21	Modeling of InGaAs/InAlAs/InP avalanche photodiodes with undepleted absorber. Proceedings of SPIE, 2012, , .	0.8	2
22	Optical examination of high contrast grating fabricated by focused-ion beam etching. Optical and Quantum Electronics, 2016, 48, 1.	1.5	1
23	Growth and characterization of InP-based 1750Ånm emitting membrane external-cavity surface-emitting laser. Applied Physics B: Lasers and Optics, 2020, 126, 1.	1.1	1
24	DW VECSEL - structure design and MBE fabrication. Photonics Letters of Poland, 2013, 5, .	0.2	1
25	<title>GaAs/AlGaAs complex structures examined by photoreflectance spectroscopy</title>. , 1997, , .		0
26	Mode structure of quantum dot semiconductor lasers. , 2004, , .		0
27	VECSELs emitting at 976nm designed for second harmonic generation in the blue wavelength region. Proceedings of SPIE, 2013, , .	0.8	0
28	PÅ³Å,przewodnikowe lasery dyskowe i€-korzyÅci z inÅ¼ynierii przerwy wzbronionej. Przegląd Elektrotechniczny, 2015, 1, 145-148.	0.1	0